

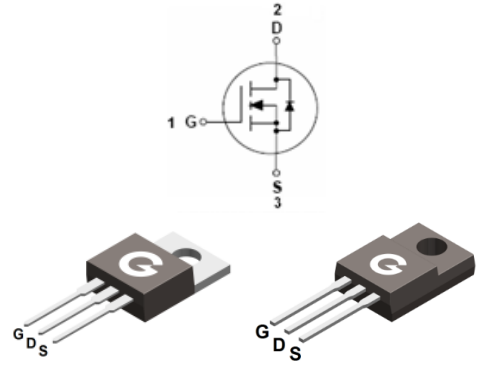
Features

- Fast switching
- Low gate charge
- Low Reverse transfer capacitances
- HBM: JESD22-A114-B: 1B

HF

Mechanical Data

- Case: TO-220AB, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; solderability-per MIL-STD-202, Method 208



TO-220AB

ITO-220AB

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL10N70	TO-220AB	50 pcs / Tube	10N70
BL10N70F	ITO-220AB	50 pcs / Tube	10N70F

Maximum Ratings (@ $T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	700	V
Gate-to-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	10	A
Continuous Drain Current ($T_c = 100^\circ\text{C}$)		6.3	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_c = 25^\circ\text{C}$)	I_{DM}	40	A
Single Pulse Avalanche Energy ²	E_{AS}	600	mJ
Power Dissipation (TO-220AB, $T_c = 25^\circ\text{C}$)	P_D	125	W
Power Dissipation (ITO-220AB, $T_c = 25^\circ\text{C}$)		40	W
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case (TO-220AB)	$R_{\theta JC}$	-	-	1	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case (ITO-220AB)		-	2.3	3.1	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air (TO-220AB)	$R_{\theta JA}$	-	-	50	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air (ITO-220AB)		-	-	62.5	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	700	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 700V, V_{GS} = 0V$	-	-	10	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*1}	$V_{GS} = 10V, I_D = 5A$	-	0.87	1.1	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	4.6	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	1642	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 25V$	-	116	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 1MHz$	-	1.8	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time ^{*3}	$V_{DD} = 350V$	-	25.6	-	ns
t_r	Turn-on Rise Time ^{*3}	$V_{GS} = 10V$	-	24.8	-	
$t_{d(OFF)}$	Turn-Off Delay Time ^{*3}	$I_D = 10A$	-	48.2	-	
t_f	Turn-Off Fall Time ^{*3}	$R_G = 10\Omega$	-	30.4	-	
Q_G	Total Gate-Charge	$V_{DD} = 560V$	-	30.5	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	7.8	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 10A$	-	10.9	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*1}	$I_{SD} = 10A, V_{GS} = 0V$	-	0.87	1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 10A, V_{GS} = 0V$	-	550	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	5.7	-	μC

Notes:

1. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
2. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100V, V_{GS} = 15V, L = 50mH$
3. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

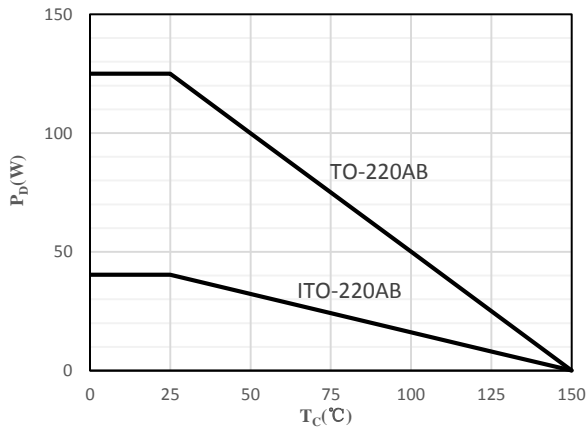


Fig 1 Power Dissipation

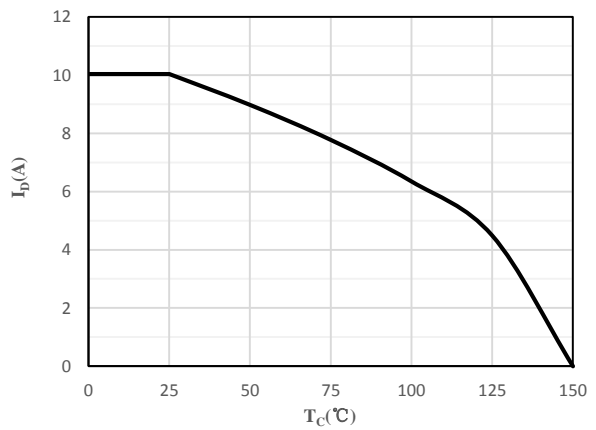


Fig 2 Drain Current

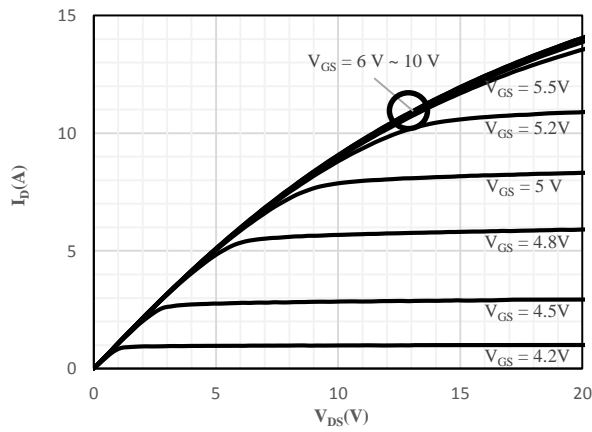


Fig 3 Typical Output Characteristics

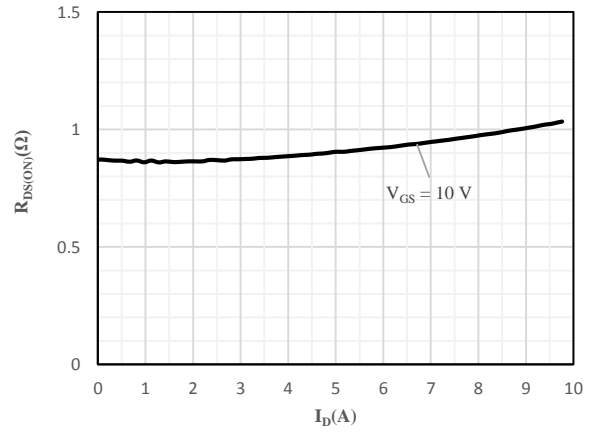


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

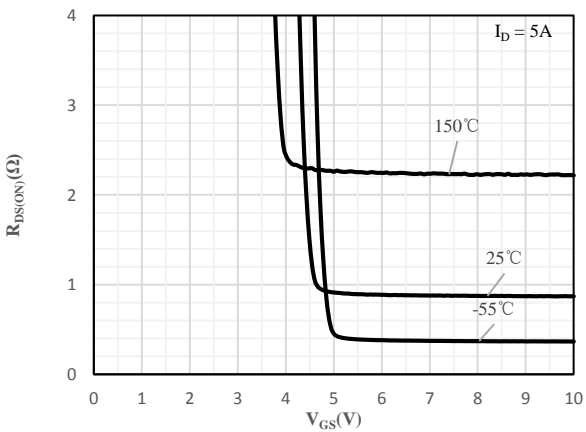


Fig 5 On-Resistance vs. Gate-Source Voltage

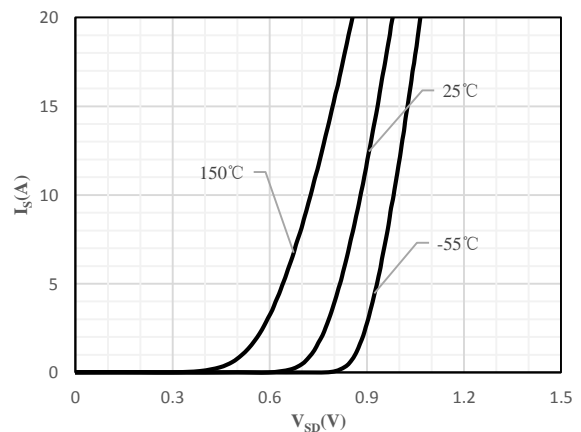


Fig 6 Body-Diode Characteristics

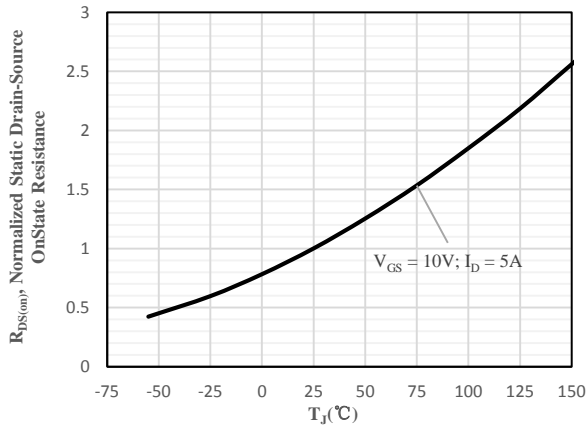


Fig 7 Normalized On-Resistance vs. Junction Temperature

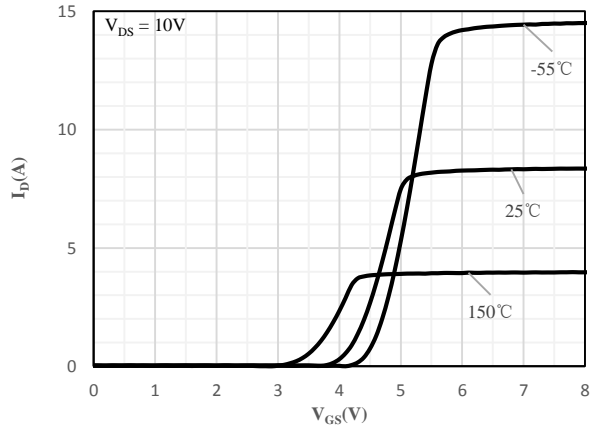


Fig 8 Transfer Characteristics

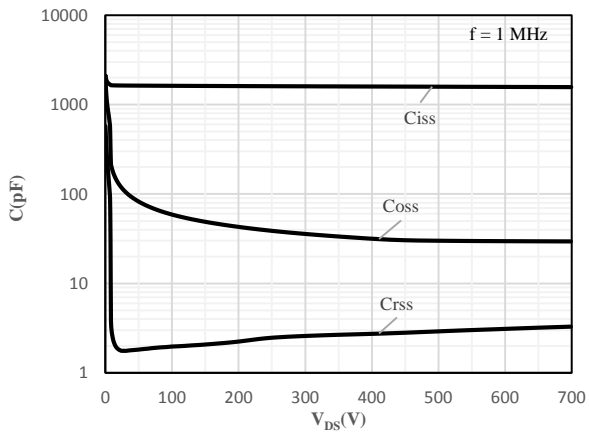


Fig 9 Capacitance Characteristics

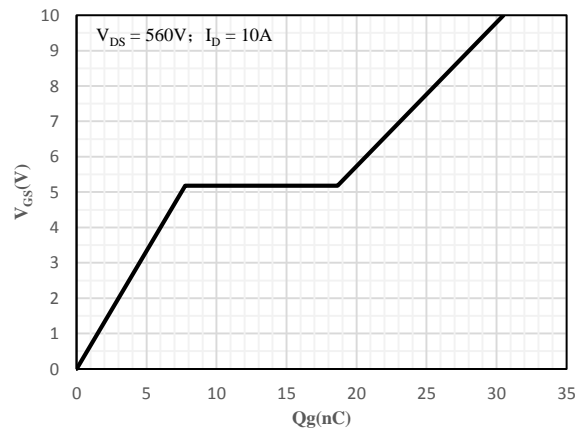


Fig 10 Gate-Charge Characteristics

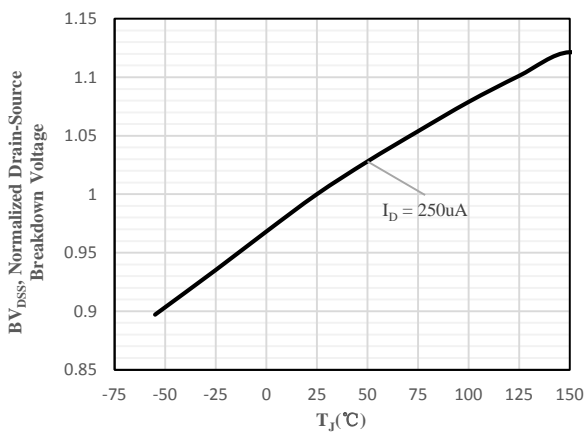


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

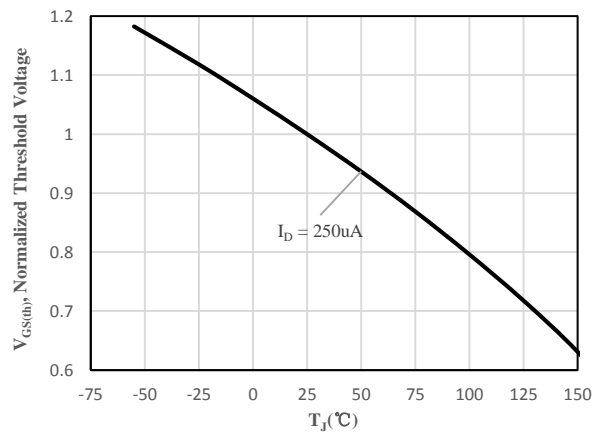


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

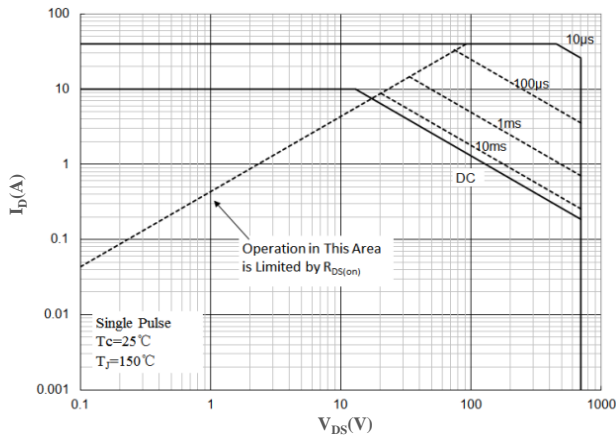


Fig 13 Safe Operation Area (TO-220AB)

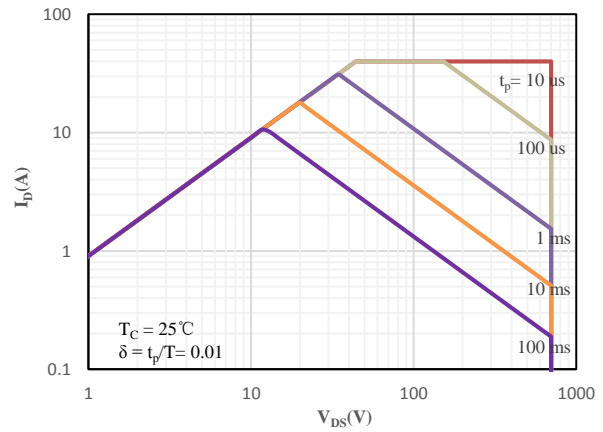


Fig 14 Safe Operation Area (ITO-220AB)

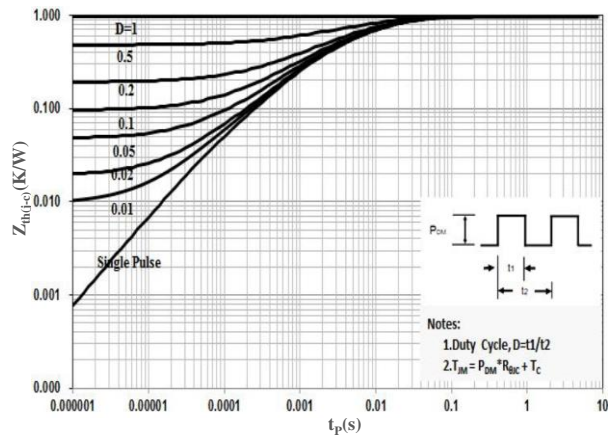


Fig 15 Maximum transient thermal impedance
(TO-220AB)

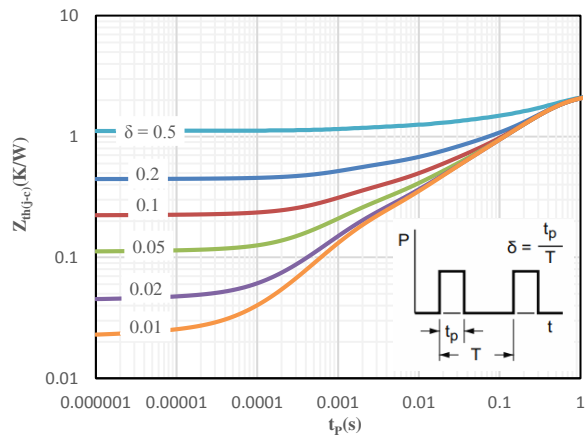


Fig 16 Maximum transient thermal impedance
(ITO-220AB)

Package Outline Dimensions (Unit: mm)

		TO-220AB		
Dimension		Min.	Max.	
A		9.80	10.30	
B		8.70	9.10	
C		4.37	4.77	
D		1.07	1.47	
E		2.64	2.84	
F		13.14	13.74	
G		2.44	2.64	
H		28.03	28.83	
I		3.50	4.00	
J		0.28	0.48	
K		1.22	1.32	
L		0.71	0.91	
M		2.40	2.60	
N		3.76	3.96	

		ITO-220AB		
Dimension		Min.	Max.	
A		9.90	10.30	
B		14.80	15.20	
C		4.30	4.70	
D		2.50	2.90	
E		2.80	3.30	
F		13.00	13.60	
G		3.10	3.30	
H		28.00	28.60	
I		7.90	8.90	
J		0.40	0.60	
L		0.70	0.90	
M		1.30	1.50	
N		2.60	2.80	
O		2.60	3.10	
P		2.45	2.65	
K/R		1.10	1.30	

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